

**AMENDMENTS****In The Claims**

Please replace the following clean copy text for claim of the same pending number:

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B4

15. A method of forming a contact opening in a semiconductor device comprising at least a first gate and a second gate, with sidewall spacers, over a substrate, and a thin liner oxide layer disposed conformal to the surface profile of the substrate and the said first and second gates, the method comprising the steps of:

forming a dielectric layer over the semiconductor device; and  
patterning the dielectric layer without planarizing the dielectric layer, to form a self-aligned contact window between the said first and second gates.

**REMARKS****Present Status of the Application**

The Office Action mailed June 28, 2002, rejected all presently pending claims 1~19 under 35 U.S.C. 103(a) as being unpatentable over Yoon et al. (US 6,117,766) in view of Jeong (US 5,960,310). Claim 5 has been amended to more accurately describe the invention. An annotated version of claims 4 and 7 illustrating the changes made thereto is attached hereto as Exhibit A. It is believed no new matter has been added to the application by the amendments made to the claims or otherwise in the application. Reconsideration of those claims is respectfully requested.

**Summary of Applicant's Invention**